

MMIC SURFACE MOUNT Wideband LNA

AVA-0233LN+

Mini-Circuits

500 2 to 30 GHz

THE BIG DEAL

- Wide Bandwidth, 2 to 30 GHz
- Flat Gain Response, Typ. 16.3 dB ± 1 dB
- Noise Figure, Typ. 2.4 dB
- 5x5mm 32-Lead SMT Package
- Gain Control, Typ. 30 dB



Generic photo used for illustration purposes only CASE STYLE: DG1677-4

+RoHS Compliant The +Suffix identifies RoHS Compliance our website for methodologies and qualified

APPLICATIONS

- 5G MIMO and Back Haul Radio Systems
- Satellite Ka-Band Communications
- Test and Measurement Equipment
- Radar, EW, and ECM Defense Systems

PRODUCT OVERVIEW

The AVA-0233LN+ is a GaAs pHEMT MMIC Distributed Amplifier that operates from 2 to 30 GHz. The amplifier provides solid performance of 16.3 dB gain, 2.4 dB noise figure, +13.6 dB P1dB, and +25.7 dBm OIP3 from a self-biased single +5V supply drawing only 65 mA. The control voltage bias input VC enables the gain to be varied by over 30 dB across the operating band. The AVA-0233LN+ MMIC amplifier is housed in an industry standard 5x5mm QFN-style package, with RF ports internally matched to 50Ω , facilitating easy integration into microwave system PC boards.

KEY FEATURES

Features	Advantages	
Wideband response with adjustable Gain: 2-30 GHz, Typ. Gain 16.3 dB, 30 dB dynamic range	General purpose wideband amplifier with adjustable gain vs. control voltage is suitable for wide variety of applications.	
Noise Figure: 2 dB Typ. 6-20 GHz 4 dB Typ. 2-30 GHz	Usable as first or second stage amplifier.	
OIP3: +26 dBm Typ. 2-20 GHz +23 dBm Typ. 20-30 GHz	— Easy to integrate into signal chain.	
Return Loss 15 dB Typ. 2-20 GHz 10 dB Typ. 20-30 GHz		
5 x 5mm 32-Lead QFN-style package	Small footprint saves space in dense layouts while providing low inductance, repeatable transitions, and excellent thermal contact to the PCB.	





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ELECTRICAL SPECIFICATIONS¹ AT 25°C, Zo=50Ω, VDD=+5V, VC = OPEN, UNLESS NOTED OTHERWISE.

Parameter	Condition (GHz)	Min.	Тур.	Max.	Units
Frequency Range		2		30	GHz
	2	16.9	17.2	17.8	
	10	15.8	16.7	17.4	
Gain	20	15.2	16.3	17.3	dB
	28	12.9	14.7	16.5	
	30	12.7	15.5	17.5	
	2		20.0		
	10		14.8		
Input Return Loss	20		12.5		dB
	28		8.9		
	30		17.2		
	2		11.5		
	10		19.3		
Output Return Loss	20		13.1		dB
	28		6.5		
	30		11.4		
Reverse Isolation	2-30		37.0		dB
	2		+16.4		
	10		+15.1		
Output Power @ 1 dB Compression	20		+13.6		dBm
	28		+11.5		
	30		+11.5		
	2		+28.4		
	10		+27.0		
Output Third-Order Intercept	20		+25.7		dBm
	28		+22.5		
	30		+20.6		
	2		4.2		
	10		1.5		
Noise Figure	20		2.4		dB
	28		4.5		
	30		4.8		
Device Operating Voltage (VDD)		+4.75	+5	+5.25	V
Device Operating Current (IDD)			65	92	mA
Device Control Voltage (VC)		-1.2	Open	+2.4	V
Gain Variation over Control Voltage (VC) ⁴ over -1.2V to 0V	2-30		30		dB
Gain Variation over Control Voltage (VC) ⁴ over 0V to +2.4V	2-30		1		dB
Device Current (IDD) Variation vs. Temperature ²			-10		μA/°C
Device Current (IDD) Variation vs. Voltage ³			0.0128		mA/mV
Thermal Resistance, Junction-to-Ground-Lead (OJC)			14.7		°C/W

1. Measured on Mini-Circuits Characterization Test Board TB-AVA-0233LNC+. See Characterization and Application Circuit (Fig.1).

Device Current Variation vs. Temperature = (Current in mA at +85°C – Current in mA at -45°C)/+130°C
Device Current Variation vs. Voltage = (Current in mA at +5.25V – Current in mA at +4.75V) / (+5.25V-+4.75V)*1000mA/mV)

4. Gain is nominal when VC = Open. When VC is left floating, there is a measured voltage of +2V on the pin. To reduce gain, add a negative bias.

MAXIMUM RATINGS⁵

Parameter	Ratings
Operating Case Temperature	-45°C to +85°C
Storage Temperature	-65°C to +150°C
Total Power Dissipation	1.55W
Junction Temperature	+150°C
RF Input Power (CW)	+20 dBm
DC Voltage at VDD	+8V
DC Voltage at VC	-2.5V to +3V
Current IDD	140mA
Current IC	5mA
DC Voltage on RE-IN and RE-OUT	+18V

5. Permanent damage may occur if any of those limits are exceeded. Electrical maximum ratings are not intended for continuous normal operation.



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SIMPLIFIED SCHEMATIC AND PAD DESCRIPTION





Function	Pad Number	Description (Refer to Figure 1)
RF-IN	6	RF-Input Pad connects to RF-Input through an integrated shunt resistor for ESD protection and DC blocking capacitor.
RF-OUT	20	RF-Output Pad connects to RF-Output through an integrated shunt resistor for ESD protection and DC blocking capacitor.
VDD	29	DC Input Pad connects to the voltage input of the device and passes through C2 and an integrated capacitor.
VC	31	Control Voltage Bias Pad connects to the control voltage input of the device and passes through C1 and an integrated capacitor. Contact Mini-Circuits Applications for more information on VC usage.
Ground	1, 8, 9, 16, 17, 24, 25, 32	Connects to ground.
No Connection	2 - 5, 7, 10 - 15, 18, 19, 21 - 23, 26 - 28, 30	Not used internally. Connected to ground on test board.

CHARACTERIZATION TEST & APPLICATION CIRCUIT



Fig 1. Characterization and Application Circuit

Note: This block diagram is used for characterization (DUT is soldered on Mini-Circuits Test Board TB-AVA-0233LNC+). Gain, Return Loss, Output Power at 1dB Compression (P1dB), Output IP3 (OIP3) and Noise Figure measured using Keysight PNA-X N5247B Microwave Network Analyzer.

Conditions:

1. VDD = +5V, VC = Open

2. Gain and Return Loss P_{IN} = -25 dBm 3. Output IP3 (OIP3): Two Tones, spaced 1 MHz apart, 0 dBm/Tone at output.

Component	Size	Value	Manufacturer	P/N
C1, C2	0402	0.1uF	Murata	GRM155R71C104KA88D

PRODUCT MARKING



Marking may contain other features or characters for internal lot control

Mini-Circuits



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Mini-Circuits

2000

6000

10000

14000

FREQUENCY (MHz)

18000

22000

26000

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TYPICAL PERFORMANCE CURVES



Mini-Circuits

30000

2000

6000

10000

14000

22000

18000 FREQUENCY (MHz) 26000

30000

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TYPICAL PERFORMANCE CURVES







P1dB vs. FREQUENCY & DEVICE VOLTAGE @ Temperature = +25°C





NOISE FIGURE vs. FREQUENCY & DEVICE VOLTAGE @ Temperature = +25°C





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VC CONTROL VS. GAIN, FREQUENCY, & CONTROL CURRENT





1. Gain is nominal when VC = Open. When VC is left floating, there is a measured voltage of +2V on the pin. For gain at different VC levels, please see visit the View Data and View Graph pages.





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ADDITIONAL DETAILED TECHNICAL INFORMATION IS AVAILABLE ON OUR DASHBOARD. TO ACCESS CLICK HERE

	Data Table
Performance Data	Swept Graphs
	S-Parameter (S2P Files) Data Set (.zip file)
Case Style	DG1677-4 QFN-style package, exposed paddle, lead finish: PPF
Tape & Reel Standard quantities available on reel	F66 7" reels with 20, 50, 100, 200, 500 or 1000 devices
Suggested Layout for PCB Design	PL-741
Evaluation Board	TB-AVA-0233LNC+
Environmental Ratings	ENV08T10
Product Handling	The use of no-clean solder is recommended. This package cannot be subjected to aqueous wash.

ESD RATING

Human Body Model (HBM): Class 1A (250V) in accordance with ANSI/ESDA/JEDEC JS-001-2017 Charged Device Model (CDM): Class C3 (1000V) in accordance with JESD22-C101F

MSL RATING

Moisture Sensitivity: MSL3 in accordance with IPC/JEDEC J-STD-020E and IPC/JEDEC J-STD-033C.

NOTES

A. Performance and quality attributes and conditions not expressly stated in this specification document are intended to be excluded and do not form a part of this specification document.

B. Electrical specifications and performance data contained in this specification document are based on Mini-Circuit's applicable established test performance criteria and measurement instructions.

C. The parts covered by this specification document are subject to Mini-Circuits standard limited warranty and terms and conditions (collectively, "Standard Terms"); Purchasers of this part are entitled to the rights and benefits contained therein. For a full statement of the standard terms and the exclusive rights and remedies thereunder, please visit Mini-Circuits' website at www.minicircuits.com/terms/viewterm.html

